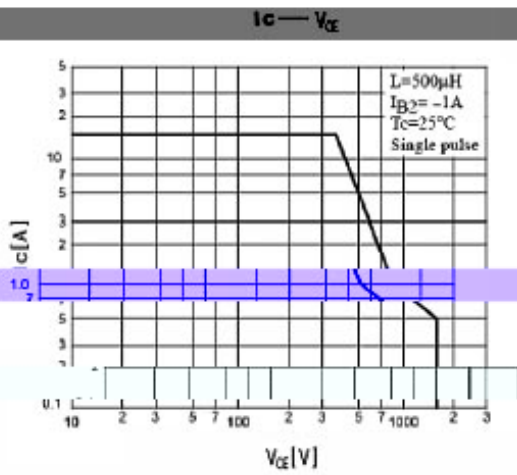
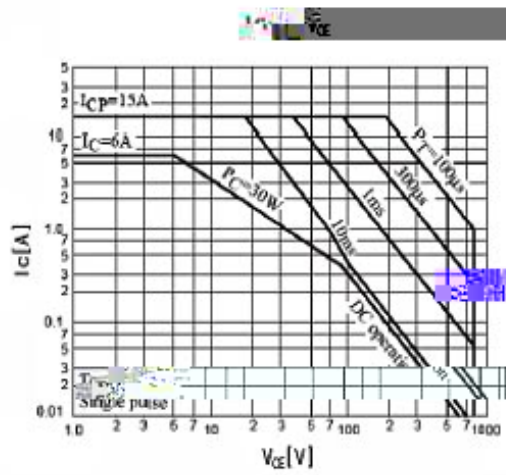
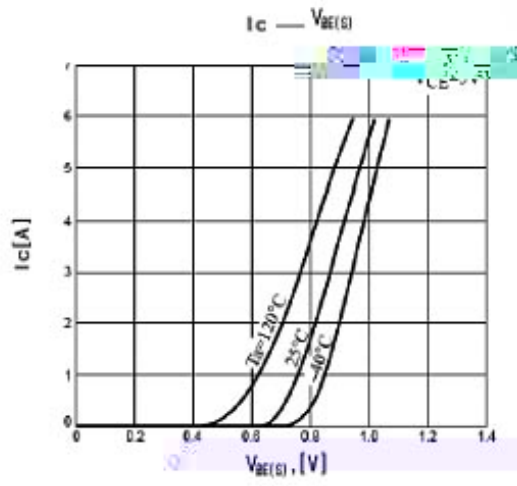
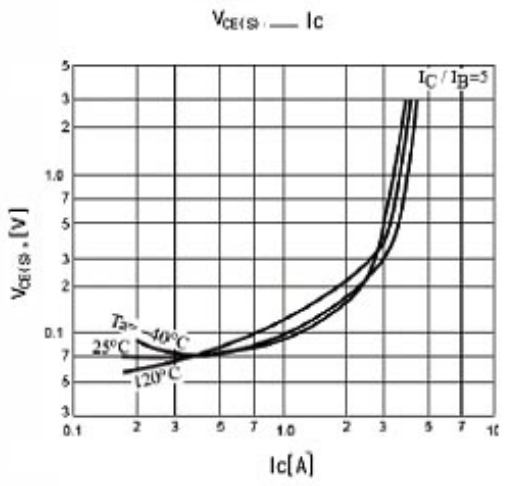
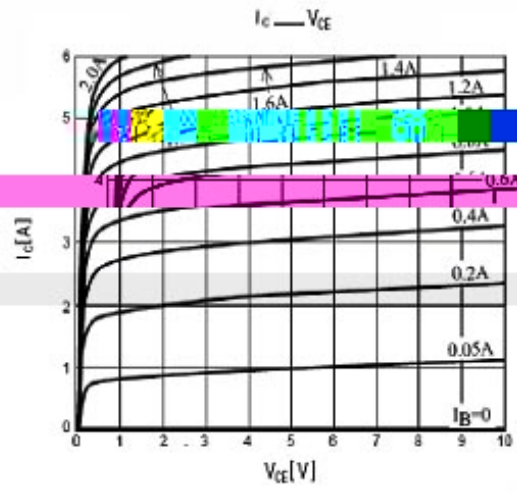
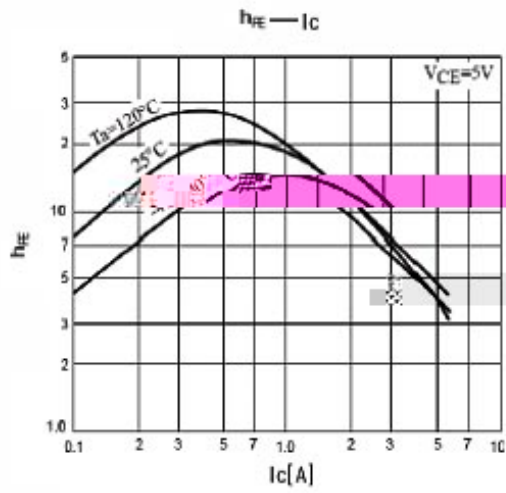


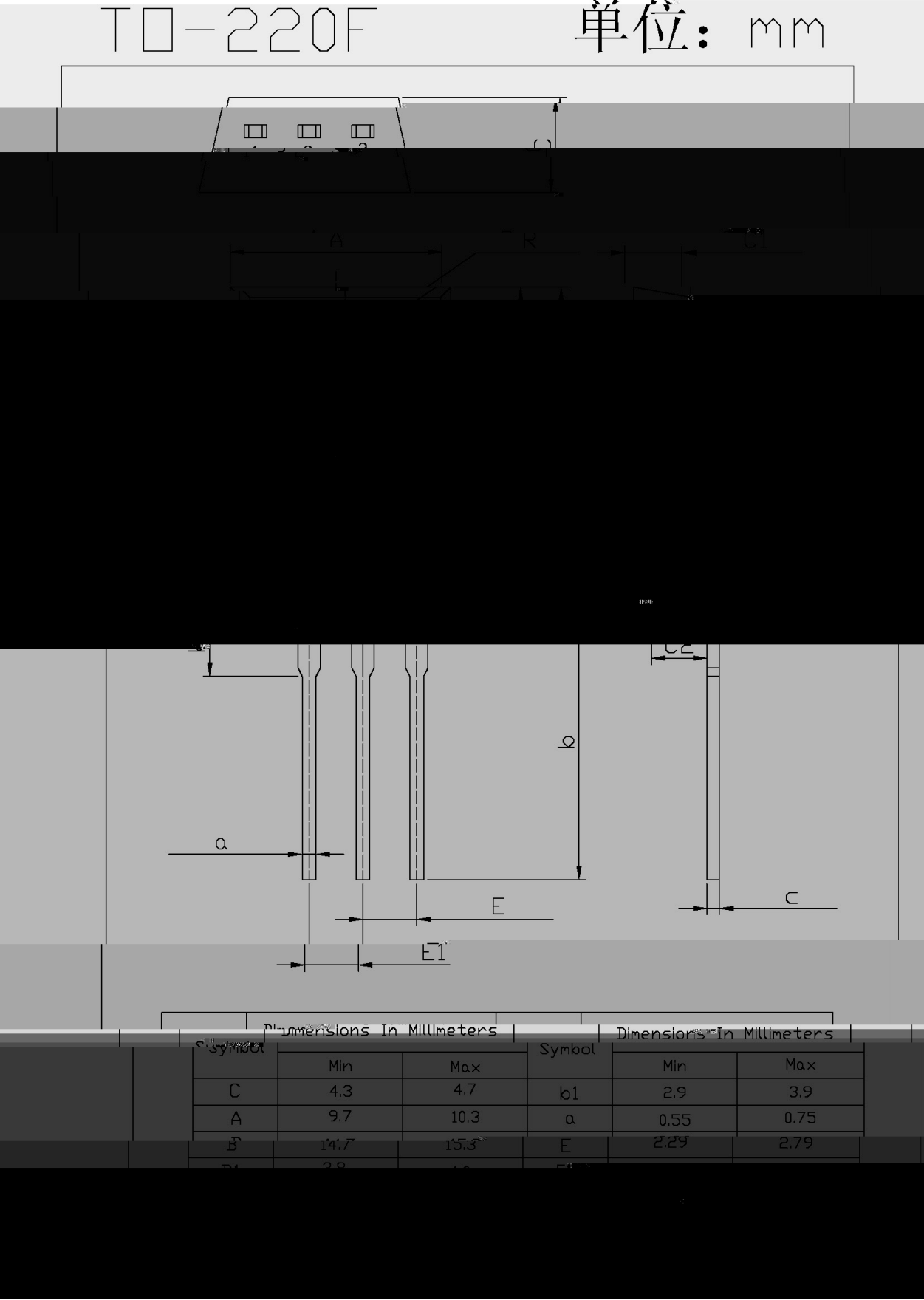
Silicon NPN transistor in a TO-220F Plastic Package.

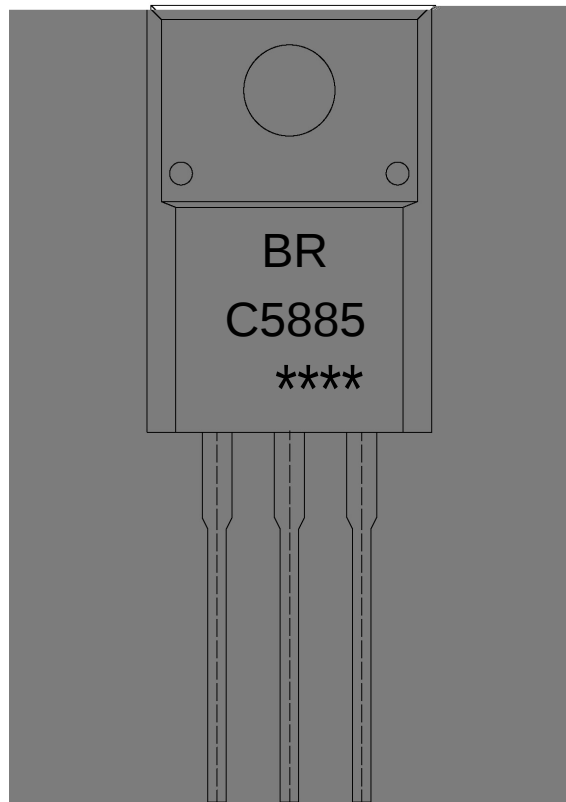
High breakdown voltage, Wide SOA, High switching speed, Low saturation voltage, Excellent current characteristics, Bulit-in dumper diode.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	1500	V
Collector to Emitter Voltage($V_{BE}=0$)	V_{CES}	1500	V
Collector to Emitter Voltage	V_{CEO}	800	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	6.0	A
Peak Collector Current	I_{CP}	15.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	30	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=500mA$ $I_C=0$	5.0			V
Forward Voltage	V_F	$I_F=3A$			2.0	V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=1000V$ $I_E=0$			50	μA
		$V_{CB}=1500V$ $I_E=0$			1.0	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=4V$ $I_C=0$	40		130	mA
DC Current Gain*	h_{FE}^*	$V_{CE}=5.0V$ $I_C=3.0A$	5		10	
Collector to Emitter Saturation Voltage*	$V_{CE(sat)}$					





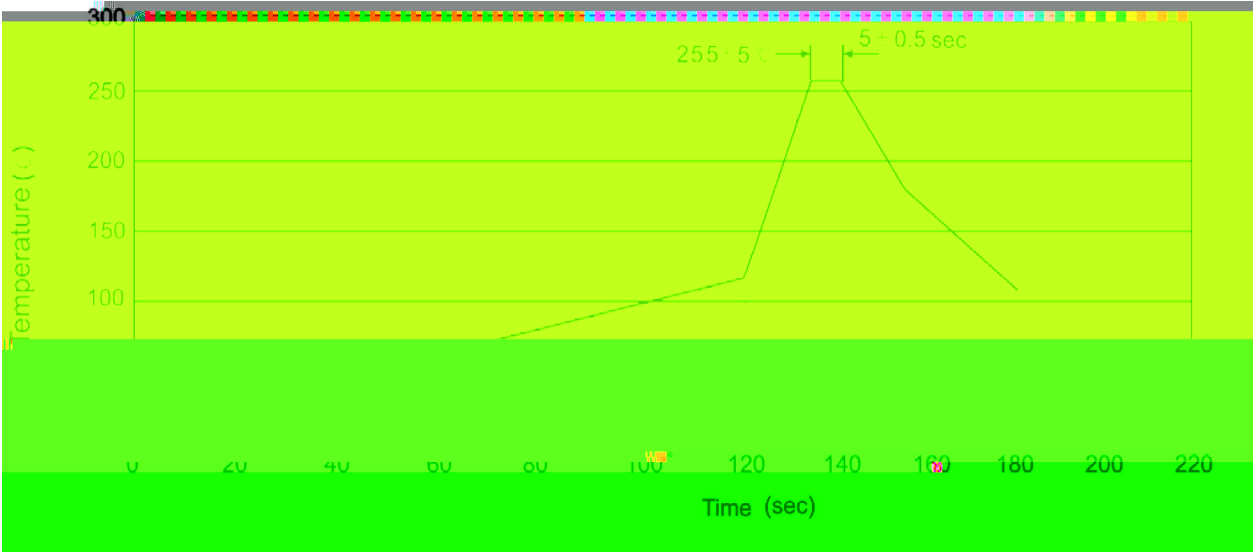


Note:

BR: Company Code

C5885: Product Type.

****: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;

2

255 5

5 0.5sec;

3

2 10

/sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

270 5

10 1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量		Dimension 包装尺寸 (unit: mm ³)
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	